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Vishay Siliconix

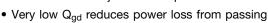
N-Channel 100 V (D-S) MOSFET

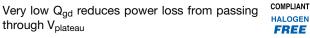


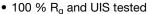
PRODUCT SUMMARY	
V _{DS} (V)	100
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.0040
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.0045
Q _g typ. (nC)	84
I _D (A)	150 ^d
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature



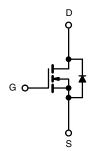




• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Switching power supply
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing / e-fuse



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and halogen-free	SUM70042E-GE3

ABSOLUTE MAXIMUM RATING	S ($T_C = 25$ °C, unle	ss otherwise noted	(k	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	100	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain surrent /T 150 °C)	T _C = 25 °C	,	150 ^d	
Continuous drain current (T _J = 150 °C)	T _C = 70 °C	l _D	139	
Pulsed drain current (t = 100 μs)		I _{DM}	200	A
Avalanche current		I _{AS}	50	
Single avalanche energy ^a	L = 0.1 mH	E _{AS}	125	mJ
Maximum navvey discination 8	T _C = 25 °C	Б	278 b	w
Maximum power dissipation ^a	T _C = 125 °C	P _D	178 ^b	T vv
Operating junction and storage temperature range		Tu Teta	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient (PCB mount) ^c	R _{thJA}	40	°C/W
Junction-to-case (drain)	R _{thJC}	0.55	J 6/VV

Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}$	100	-	-	V
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA
		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50	-	-	Α
During a second of the second	_	V _{GS} = 10 V, I _D = 20 A	-	0.0033	0.0040	0
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 7.5 V, I _D = 15 A	-	0.0036	0.0045	Ω
Forward transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A	-	60	-	S
Dynamic ^b				•		
Input capacitance	C _{iss}		-	6490	-	
Output capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	570	-	pF
Reverse transfer capacitance	C _{rss}		-	20	-	
Total gate charge ^c	Qg		-	84	110	
Gate-source charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	33.5	-	nC
Gate-drain charge ^c	Q _{gd}		-	9.5	-	
Gate resistance	Rg	f = 1 MHz	0.26	1.3	2.6	Ω
Turn-on delay time ^c	t _{d(on)}		-	25	50	
Rise time °	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 5 \Omega$	-	18	36	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	45	90	ns
Fall time ^c	t _f		-	14	28	
Drain-Source Body Diode Ratings	and Characte	ristics ^b (T _C = 25 °C)				
Pulsed current (t = 100 μs)	I _{SM}		-	-	200	Α
Forward voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V
Reverse recovery time	t _{rr}		-	58	116	ns
Peak reverse recovery charge	I _{RM(REC)}		-	3.9	5.9	Α
Reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	126	189	μC
Reverse recovery fall time	t _a		-	42	-	ns
Reverse recovery rise time	t _b	t _b -		16	-	113

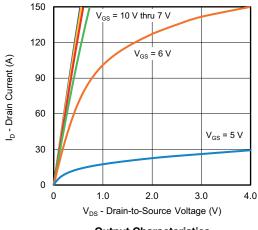
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

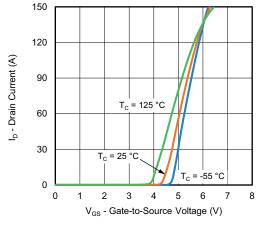
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



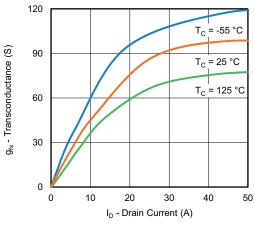
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



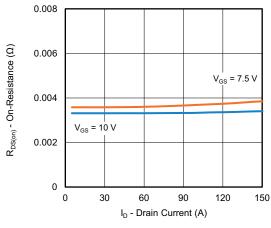
Output Characteristics



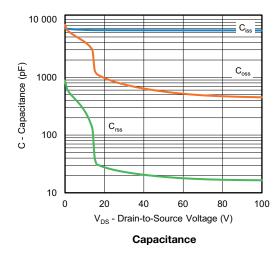
Transfer Characteristics

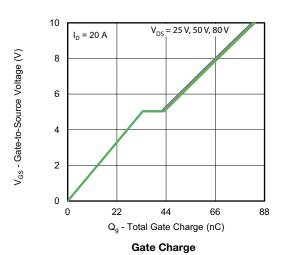


Transconductance



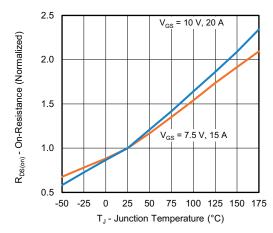
On-Resistance vs. Drain Current



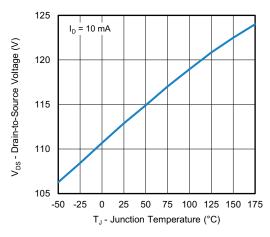




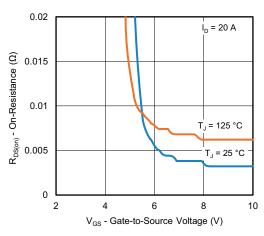
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



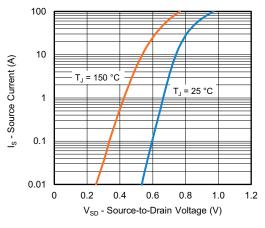
On-Resistance vs. Junction Temperature



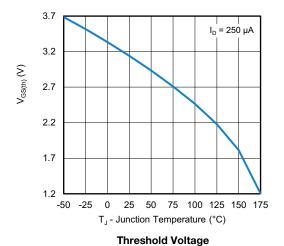
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

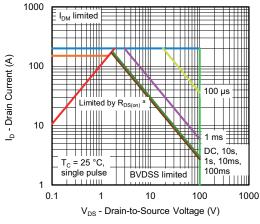


Source Drain Diode Forward Voltage





THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)





10

0.000001

0.00001

100

25 °C

0.0001

t - Time (s)

0.001

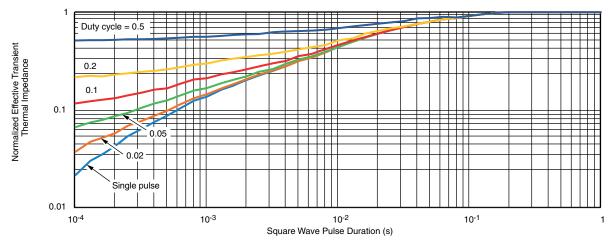
0.01

I_{DAV} - Drain Current Avalanche (A)

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

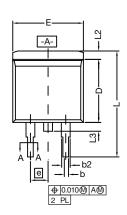
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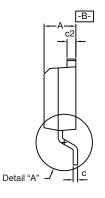
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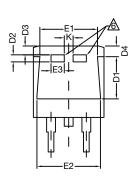


TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

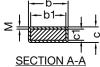








DETAIL A (ROTATED 90°)



≥ <u>↓</u>			ţ
< T		10	ပ
SF	CTION	1	1

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INC	HES	MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
А		0.160	0.190	4.064	4.826
b		0.020 0.039 0		0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
١	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
Ü	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100 BSC		2.54	BSC
	K 0.045 0.055 1.143		1.397		
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050

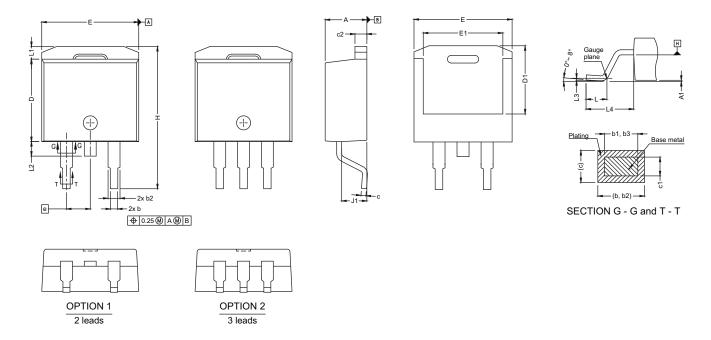
Revison: 28-Oct-2024 Document Number: 71198



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VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
С	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
е	2.54	BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25	5 typ.
L4	4.78	5.28
J1	2.56	2.96

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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